

Non-Volatile Memory Technology Compatible With 1T-RAM Process

ABSTRACT OF THE DISCLOSURE

Methods of fabricating memory devices having non-volatile and volatile memory are provided. A substrate is provided, wherein the substrate has a non-volatile memory region and a volatile memory region. The non-volatile memory region has a storage device, such as a split-gate transistor, that is fabricated in substantially the same process steps as a storage capacitor of the volatile memory region. The reduction of process steps allow mixed memory to be fabricated in a cost effective manner.